

- 9.** A catalyst comprising:  
an aluminide-containing substrate;  
a dense and substantially defect-free alumina layer disposed on the aluminide-containing substrate; and  
a catalyst material directly disposed on the thermally-grown alumina layer.
- 10.** The catalyst of claim 9 wherein the dense and substantially defect-free alumina layer comprises a thermally-grown alumina layer.
- 11.** A process for converting ethane to ethylene, comprising:  
contacting ethane and oxygen in a reaction microchannel;  
wherein the reaction microchannel comprises a catalyst coated on a substrate;  
wherein (a) at least 50% of the ethane entering the reaction microchannel is converted to products and the selectivity to ethene is at least 85%; or  
(b) at least 70% of the ethane entering the reaction microchannel is converted to products and the selectivity to ethene is at least 80%; and  
wherein the levels of selectivity and conversion are based on a single pass through the reaction microchannel.
- 12.** The process of claim 11 wherein the substrate comprises a wall of the reaction microchannel, and further comprising removing heat from the reaction microchannel into an adjacent heat exchanger.
- 13.** The process of claim 12 wherein at least about 80% of the ethane entering the reaction microchannel is converted to products.

- 14.** The process of claim 12 wherein the adjacent heat exchanger comprises a microchannel heat exchanger.
- 15.** The process of claim 11 wherein the selectivity to ethene is in the range of 84% to about 93%.
- 16.** The process of claim 12 wherein the reaction microchannel comprises a metallic microchannel wall;  
wherein the metallic microchannel wall is coated with an aluminide layer;  
wherein the aluminide layer is coated with a dense and substantially defect-free alumina layer surface layer;  
and  
wherein a catalytic material is directly disposed on the surface layer.
- 17.** The process of claim 17 wherein the dense and substantially defect-free alumina layer comprises a thermally-grown alumina layer.
- 18.** A process for oxidative dehydrogenation, comprising:  
passing an alkane over a fixed catalyst comprising Pt and Sn in a Pt/Sn atomic ratio in the range of 1 to 4 directly disposed on a thermally-grown oxide layer.
- 19.** The method of claim 18 wherein the catalyst comprises Pt and Sn in a Pt/Sn atomic ratio in the range of about 2.3 to about 2.5.
- 20.** The method of claim 18 wherein the fixed catalyst consists essentially of Pt and Sn on a dense and substantially defect-free alumina layer.

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